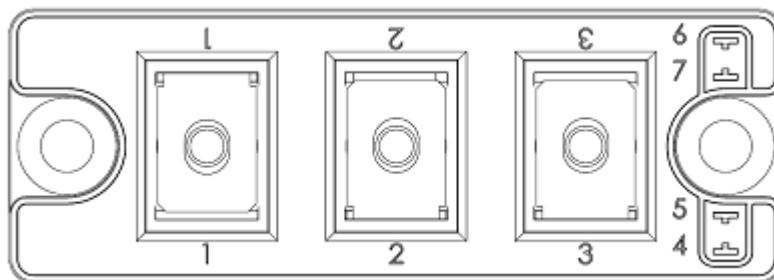
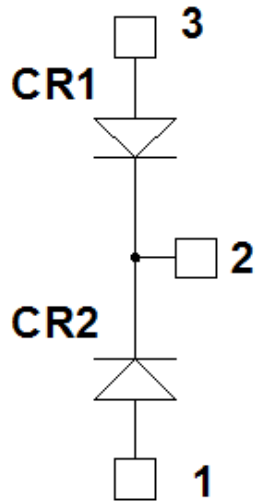


MSCDC100KK70D1PAG Dual Common Cathode SiC Diodes Power Module

1 Product Overview

This section shows the product overview of the MSCDC100KK70D1PAG device.



All ratings at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

1.1 Features

The following are key features of the MSCDC100KK70D1PAG device:

- Silicon carbide (SiC) Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- M5 power connectors
- Aluminum nitride (AlN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC100KK70D1PAG device:

- Stable temperature behavior
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC100KK70D1PAG device is designed for the following applications:

- Welding converters
- Switched mode power supplies
- Uninterruptible power supplies

2 Electrical Specifications

This section shows the electrical specifications of the MSCDC100KK70D1PAG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSCDC100KK70D1PAG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{RRM}	Repetitive peak reverse voltage	700	V
I_F	DC forward current	$T_C = 70\text{ }^\circ\text{C}$ 100	A

The following table shows the thermal and package characteristics of the MSCDC100KK70D1PAG device.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
V_{ISOL}	RMS isolation voltage, any terminal to case $t = 1$ minute, 50 Hz/60 Hz	4000		V		
T_J	Operating junction temperature range	-40	175	$^\circ\text{C}$		
T_{JOP}	Recommended junction temperature under switching conditions	-40	$T_{Jmax} - 25$			
T_{STG}	Storage temperature range	-40	125			
T_C	Operating case temperature	-40	125			
Torque	Mounting torque	For terminals	M5	2	3.5	N.m
		To heatsink	M6	3	5	
W_t	Package weight			160	g	

2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC100KK70D1PAG device.

Table 3 • Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode forward voltage	$I_F = 100\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	1.5	1.8	V
			$T_J = 175\text{ }^\circ\text{C}$	1.9		
I_{RM}	Reverse leakage current	$V_R = 700\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	30	400	μA
			$T_J = 175\text{ }^\circ\text{C}$	500		
Q_C	Total capacitive charge	$V_R = 400\text{ V}$		266		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 200\text{ V}$		496		pF
		$f = 1\text{ MHz}, V_R = 400\text{ V}$		432		
R_{thJC}	Junction-to-case thermal resistance				0.456	$^\circ\text{C/W}$

2.3 Typical Performance Curves

This section shows the typical performance curves of the MSCDC100KK70D1PAG device.

Figure 1 • Maximum Transient Thermal Impedance

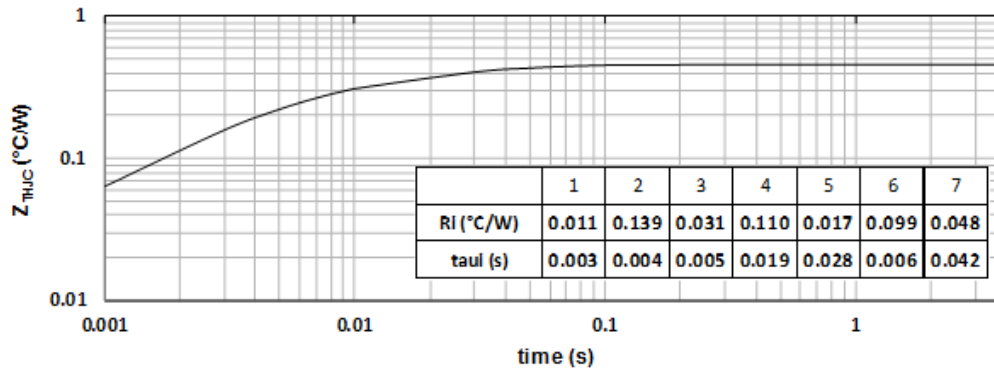


Figure 2 • Forward Current vs. Forward Voltage

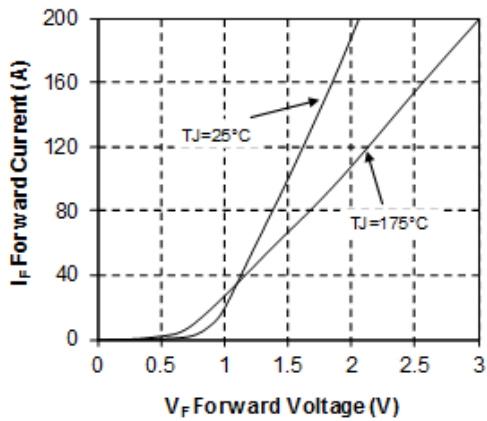
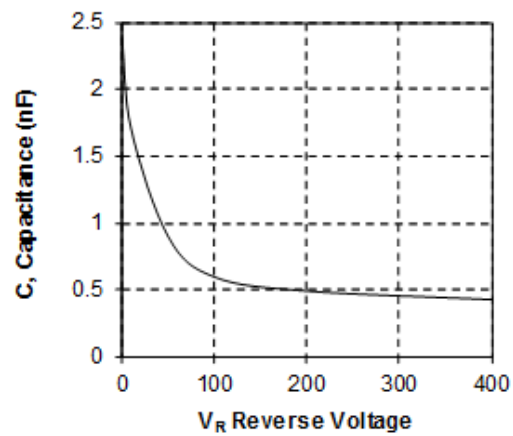


Figure 3 • Capacitance vs. Reverse Voltage



3 Package Specification

This section shows the package specifications for the MSCDC100KK70D1PAG device.

3.1 Package Outline Drawing

The package outline of the MSCDC100KK70D1PAG device is illustrated in this section. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing

